

ABSTRACT OF THE DISCLOSURE

SILICATE GATE DIELECTRIC

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- 5 A method of forming a silicate dielectric having superior  
electrical properties comprising forming a metal oxide  
layer on a Si-containing semiconductor material and  
reacting the metal oxide with the underlying Si-  
containing material in the presence of an oxidizing gas  
10 is provided. Semiconductor structures comprising the  
metal silicate formed over a  $\text{SiO}_2$  layer are also  
disclosed herein.

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